

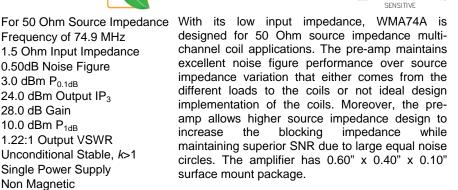
Key Features



- Frequency of 74.9 MHz
- 1.5 Ohm Input Impedance
- 0.50dB Noise Figure
- 3.0 dBm P_{0.1dB}
- 24.0 dBm Output IP₃
- 28.0 dB Gain
- 10.0 dBm P_{1dB}
- 1.22:1 Output VSWR
- Unconditional Stable, k>1
- Single Power Supply
- Non Magnetic

Specifications

Product Description



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ELECTROSTATIC DISCHARGE

Applications

Magnetic Resonance Imaging

REV B

August 2022

- **RF** Measurement
- Medical
- Current Sensor



Due to White Tin plating, Nitrogen cabinet storage is recommended. Improper storage may affect the solder ability!

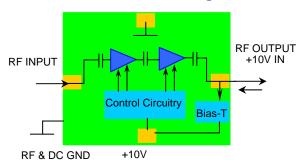
Summary of the key electrical specifications at room temperature

Index	Testing Item	Symbol	Test Constraints	Min	Nom	Max	Unit
1	Gain	S ₂₁	74.9 MHz	27	28	29	dB
2	Gain Variation	ΔG	74.9 MHz +/- 1 MHz		+/-0.05	+/- 0.1	dB
2	Input Impedance	RE [Zin]	74.9 MHz, with 80050 test fixture	1.2	1.5	2.0	Ohm
3		IM [Zin]	74.9 MHz, with 80050 test fixture	-2.0	0	2.0	Ohm
4	Output VSWR, 50 Ohm Impedance	SWR ₂	74.9 MHz			1.22:1	Ratio
5	Reverse Isolation	S ₁₂	74.9 MHz	60	70		dB
6	Noise Figure	NF	74.9 MHz, Z _s = 50 Ohm		0.5	0.6	dB
7	Output Power 0.1dB Compression Point	P _{0.1dB}	74.9 MHz	0	3		dBm
8	Output Power 1dB Compression Point	P _{1dB}	74.9 MHz	8	10		dBm
9	Output-Third-Order Interception Point	IP ₃	Two-Tone, P _{out} = 0 dBm each, 1 MHz separation	18	23		dBm
10	Current Consumption	I _{dd}	V _{dd} = +10.0 V		18		mA
11	Power Supply Operating Voltage	V_{dd}		+7	+10	+15	V
12	Thermal Resistance	R _{th,c}	Junction to case			220	°C/W
13	Operating Temperature	To		+10		+60	°C
14	Maximum RF Input Power	P _{IN, MAX}	DC – 6.0 GHz, 10% Duty Cycle, $Z_s = 50$ Ohm			30	dBm
15	Saturate Recover Time	t _{sr}	10% to 90% from 20 dBm Pin, Z _s = 50 Ohm		4	8	uS
16	ESD Protection, None Contact	V _{ESDN}	RF Output Port			16	kV
17	ESD Protection, Direct Contact	V _{ESD}	RF Output Port			6	kV

Absolute Maximum Ratings

Units	Ratings
V	16.0
mA	30
mW	350
dBm	30
°C	150
°C	-40 ~ 85
°C	0 ~ +70
°C/W	220
	V mA mW dBm °C °C °C

Functional Block Diagram



¹ The last stage transistor dominates the heat dissipation. The drain bias voltage is +3.5V and the drain current is 10.0 mA. The total power dissipation of the last stage transistor is thus 35 mW. The junction temperature arise 0.035 x 220 = 7.7 (°C).

Specifications and information are subject to change without notice.

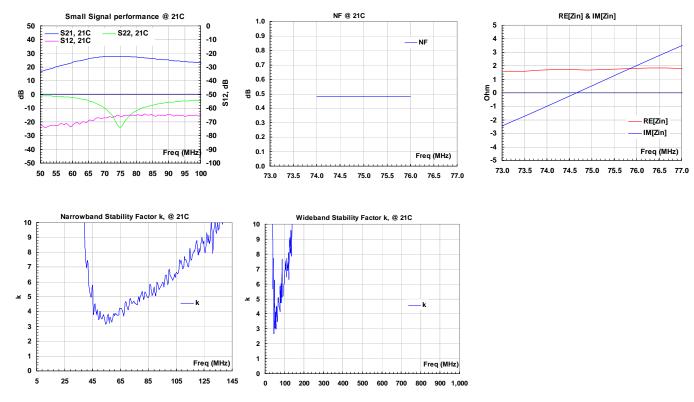


Ordering Information

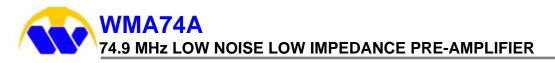
Model Number WMA74A

ESD pack is used for the packing. Contact factory for tape and reel packing option for higher volume order.

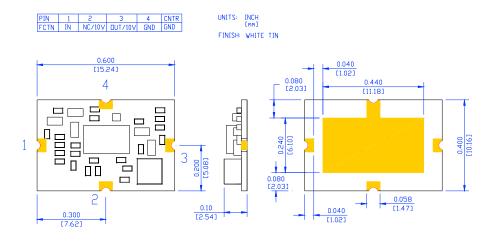
Typical Data



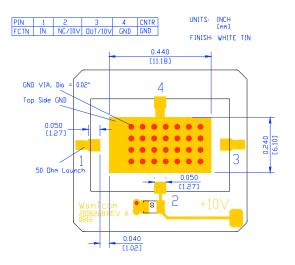
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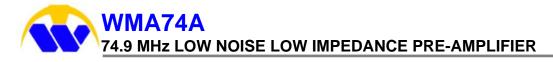
Outline,



Foot Print/Mounting Layout



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Application Notes:

A. Motherboard Layout

The recommended motherboard layout is shown in the diagram of **Foot Print/Mounting Layout**. Sufficient quantities of ground vias on center ground pad are essential for the RF grounding. The width of the 50-Ohm microstrip lines at the input and output RF ports may be different for different property of the substrate. The ground plane on the backside of the substrate is needed to connect the center ground pad through the vias. The ground plane is also essential for the 50-Ohm microstrip line launches at the input and output ports.

In order to have stable pre-amp in the coil system, the minimum system isolation of 55 dB between the input and output soldering pads for the preamp with all the components including the coils on the feed board is required. Poor system isolation can introduce external feedback either in pass band or off band and cause the pre-amp parasitic oscillation. Measure the S_{12} or S_{21} between the input and output pads without the installation of the pre-amp is essential to insure the stable preamp operation.

The +10V DC voltage can be applied at Pin 2 or at the output Pin 3. There is a built-in bias-T at the output port to separate the RF output signal and the input +10V DC power supply. Pin 2 and Pin 3 are DC connected internally.

No DC block capacitor is required at input port.

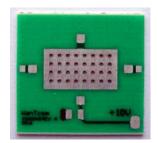


Fig. 1 Example of the test board

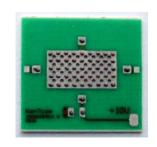


Fig. 2 Dispensed solder paste



Fig. 3 Assembled preamp

B. Assembly

The high temperature solder is used internally center chip assembly. The melting temperature point of the high temperature solder is around 240 °C. Thus, melting temperature of the solder paste should be way below 240 °C for assembling the preamp on the test board or feed board.

For high reliability product, Lead SN63/Pb63 solder paste, which melting temperature point being around 183 ⁰C, is recommended for the assembly purpose.

For RoHS requirement, Bismuth based Lead free solder paste such as 60Sn/40Bi is suitable for the assembly.

Warning: regular SAC305 RoHS reflow process will damage the pre-amp!

The solder paste can be dispensed by a needle manually or driven by a compressed air. **Figure 2** shows the example of the dispensed solder paste pattern. Each solder paste dot is in the diameter of $0.005^{\circ} \sim 0.010^{\circ}$ (0.125 ~ 0.250 mm).

For volume assembly, a stencil with 0.006" (0.15 mm) is recommended to print the solder paste on the circuit board.

For more detail assembly process, refer to AN-109 at <u>www.wantcominc.com</u> website.

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